Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	(29/852).ccls. and (semiconductor or MOSFET or electronic) and ((cavity or hole or recess or opening) near (metal or silicide or tungsten or titanium)) and ((heat or heated or heating) near (metal or silicide or tungsten or titanium))and ((planariz\$5 or remov\$3 or machin\$3) near (metal or silicide or tungsten or titanium))	US-PGPUB; USPAT; IBM_TDB	OR	ON	2006/07/24 08:49
L2	3	(29/846,847,849,853).ccls. and (semiconductor or MOSFET or electronic) and ((cavity or hole or recess or opening) near (metal or silicide or tungsten or titanium)) and ((heat or heated or heating) near (metal or silicide or tungsten or titanium))and ((planariz\$5 or remov\$3 or machin\$3) near (metal or silicide or tungsten or titanium))	US-PGPUB; USPAT; IBM_TDB	OR	ON	2006/07/24 08:50
L3	5	(257/347,351,E21.011,E21.588). ccls. and (semiconductor or MOSFET or electronic) and ((cavity or hole or recess or opening) near (metal or silicide or tungsten or titanium)) and ((heat or heated or heating) near (metal or silicide or tungsten or titanium))and ((planariz\$5 or remov\$3 or machin\$3) near (metal or silicide or tungsten or titanium))	US-PGPUB; USPAT; IBM_TDB	OR	ON	2006/07/24 08:51
L4	5	(438/3,632,655).ccls. and (semiconductor or MOSFET or electronic) and ((cavity or hole or recess or opening) near (metal or silicide or tungsten or titanium)) and ((heat or heated or heating) near (metal or silicide or tungsten or titanium))and ((planariz\$5 or remov\$3 or machin\$3) near (metal or silicide or tungsten or titanium))	US-PGPUB; USPAT; IBM_TDB	OR	ON	2006/07/24 08:52
L5	2	(438/615).ccls. and (semiconductor or MOSFET or electronic) and ((cavity or hole or recess or opening) near (metal or silicide or tungsten or titanium)) and ((heat or heated or heating) near (metal or silicide or tungsten or titanium))and ((planariz\$5 or remov\$3 or machin\$3) near (metal or silicide or tungsten or titanium))	US-PGPUB; USPAT; IBM_TDB	OR	ON	2006/07/24 08:52

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S1	44	(coronel-philippe).in.	US-PGPUB; USPAT; IBM_TDB	OR	ON	2006/07/19 15:11
S2	1	(coronel-philippe).in. and (compound adj material adj cavity)	US-PGPUB; USPAT; IBM_TDB	OR	ON	2006/07/19 15:13
S3	1	(regnier-christophe).in. and (compound adj material adj cavity)	US-PGPUB; USPAT; IBM_TDB	OR	ON	2006/07/19 15:16
S4	1	(wacquant-francois).in. and (compound adj material adj cavity)	US-PGPUB; USPAT; IBM_TDB	OR	ON	2006/07/19 15:15
S5	1	(skotnicki-thomas).in. and (compound adj material adj cavity)	US-PGPUB; USPAT; IBM_TDB	OR	ON	2006/07/19 15:15
S6	1	(regnier-christophe).in. and (compound adj material adj cavity)	US-PGPUB; USPAT; IBM_TDB	OR	ON	2006/07/19 15:42
S7	4	(("5,583,362") or ("5,120,666") or ("5,580,802") or ("20020003256")). PN.	US-PGPUB; USPAT; IBM_TDB	OR	OFF	2006/07/19 15:43
S8	40	("5120666").URPN.	USPAT	OR	ON	2006/07/20 18:00
S9	14	("4396930" "5120666" "5188973" "5273921" "5278102" "5296727" "5338959" "5574294" "5658806" "5736435" "5759878" "5926699" "6004837" "6207530").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/07/20 18:18
S10	156806	(semiconductor or MOSFET or electronic) and (cavity or hole or recess or opening) and (metal or silicide or tungsten or titanium) and (heat or heated or heating) and (planariz\$5 or remov\$3 or machin\$3)	US-PGPUB; USPAT; IBM_TDB	OR	ON	2006/07/20 19:14
S11	40245	(semiconductor or MOSFET or electronic) and ((cavity or hole or recess or opening) with (metal or silicide or tungsten or titanium)) and (heat or heated or heating) and (planariz\$5 or remov\$3 or machin\$3)	US-PGPUB; USPAT; IBM_TDB	OR	ON	2006/07/20 19:15

S12	15826	(semiconductor or MOSFET or electronic) and ((cavity or hole or recess or opening) with (metal or silicide or tungsten or titanium)) and ((heat or heated or heating) with (metal or silicide or tungsten or titanium))and (planariz\$5 or remov\$3 or machin\$3)	US-PGPUB; USPAT; IBM_TDB	OR	ON	2006/07/20 19:15
S13	8990	(semiconductor or MOSFET or electronic) and ((cavity or hole or recess or opening) with (metal or silicide or tungsten or titanium)) and ((heat or heated or heating) with (metal or silicide or tungsten or titanium))and ((planariz\$5 or remov\$3 or machin\$3) with (metal or silicide or tungsten or titanium))	US-PGPUB; USPAT; IBM_TDB	OR	ON	2006/07/20 19:16
S14	1252	(semiconductor or MOSFET or electronic) and ((cavity or hole or recess or opening) with (metal or silicide or tungsten or titanium)) and ((heat or heated or heating) near (metal or silicide or tungsten or titanium))and ((planariz\$5 or remov\$3 or machin\$3) with (metal or silicide or tungsten or titanium))	US-PGPUB; USPAT; IBM_TDB	OR	ON	2006/07/20 19:16
S15	85	(semiconductor or MOSFET or electronic) and ((cavity or hole or recess or opening) near (metal or silicide or tungsten or titanium)) and ((heat or heated or heating) near (metal or silicide or tungsten or titanium))and ((planariz\$5 or remov\$3 or machin\$3) near (metal or silicide or tungsten or titanium))	US-PGPUB; USPAT; IBM_TDB	OR	ON	2006/07/24 08:48
S16	54	("5736435").URPN.	USPAT	OR	ON	2006/07/20 19:26
S17	97	(semiconductor or MOSFET or electronic) and ((cavity or hole or recess or opening or trench) near (metal or silicide or tungsten or titanium)) and ((heat or heated or heating) near (metal or silicide or tungsten or titanium))and ((planariz\$5 or remov\$3 or machin\$3) near (metal or silicide or tungsten or titanium))	US-PGPUB; USPAT; IBM_TDB	OR	ON	2006/07/21 09:33
S18	1	("6001660").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/07/21 09:53

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S19	1290435	silicon with heat\$3 with silicide convert\$3	US-PGPUB; USPAT; IBM_TDB	OR	ON	2006/07/21 11:56
S20	168	silicon with heat\$3 with silicide with convert\$3	US-PGPUB; USPAT; IBM_TDB	OR	ON	2006/07/21 11:56